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(72) Inventors; and

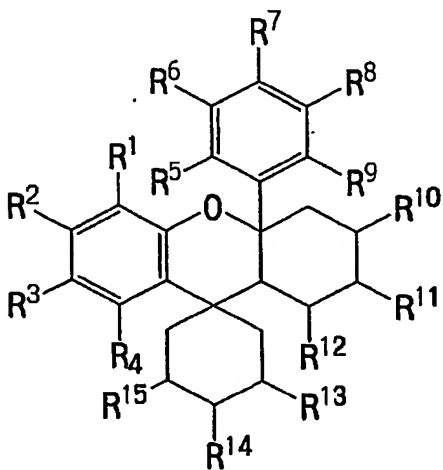
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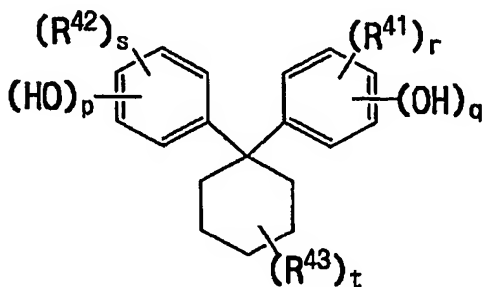
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(54) Title: POSITIVE PHOTORESIST COMPOSITION AND METHOD OF FORMING RESIST PATTERN



... (b-1)

(57) Abstract: There is provided a positive photoresist composition capable of forming a pattern with excellent resolution, excellent resistance to reflection off the substrate, and excellent perpendicularity. The positive photoresist composition comprises (A) an alkali-soluble novolak resin in which a portion of the hydrogen atoms of all the phenolic hydroxyl groups are substituted with 1,2-naphthoquinonediazidesulfonyl groups, and (B) a dissolution promoter represented by a general formula (b-1) and/or a general formula (b-11) shown below.



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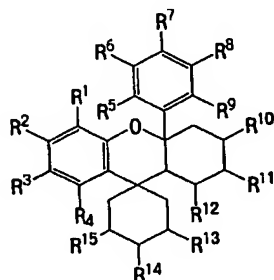
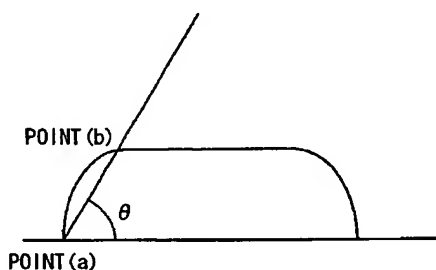
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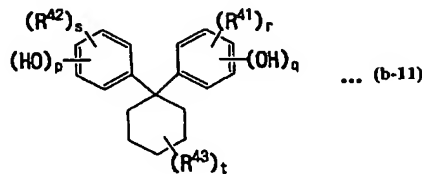
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